UNISONIC TECHNOLOGIES CO., LTD

UTG7N65ND-S

Preliminary

Insulated Gate Bipolar Transistor

650V TRENCH GATE FIELD-STOP IGBT

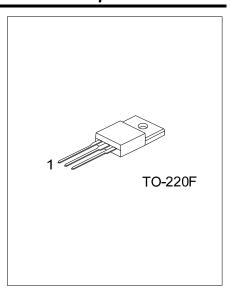
DESCRIPTION

The UTC **UTG7N65ND-S** is an Trench Field-Stop Insulated Gate Bipolar Transistor. it uses UTC's advanced technology to provide customers with high switching speed, low saturation voltage and low switching loss, etc.

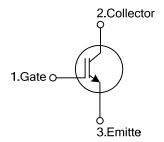
The UTC **UTG7N65ND-S** is suitable for the resonant or soft switching applications.



- * High switching speed
- * High avalanche ruggedness
- * Low saturation voltage: $V_{CE(SAT).Typ.}=1.6V$ @ $I_C=7.0A$, $V_{GE}=15V$ ($T_C=25^{\circ}C$)



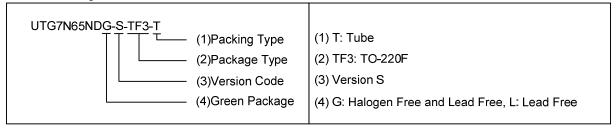
■ SYMBOL



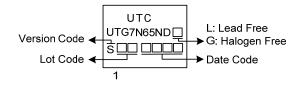
■ ORDERING INFORMATION

Ordering Number		Daalaana	Pin Assignment			Da alsimum	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UTG7N65NDL-S-TF3-T	UTG7N65NDG-S-TF3-T	TO-220F	G	С	E	Tube	

Note: Pin Assignment: G: Gate C: Collector E: Emitter



■ MARKING



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ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Emitter Voltage	ector-Emitter Voltage		650	V
Gate-Emitter Voltage		V	±20	V
Transient Gate-emitter voltage (tp < 5 ms)		V_{GES}	±25	V
Continuous Collector Current	T _C =25°C	lc	14	Α
	T _C =100°C		7	Α
Collector Current Pulsed (Note 1)		I _{CM}	I _{CM} 28	
Diode Forward Current	T _C =25°C		14	Α
	T _C =100°C	I _F	7	Α
Power Dissipation (T _C =25°C)		P _D	25	W
Operating Junction Temperature		TJ	-40 ~ +150	°C
Storage Temperature Range		T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are stress ratings only and functional device operation is not implied. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Case	θις	5	°C/W

Note: Device mounted on FR-4 substrate Pc board, 2oz copper, with 1inch square copper plate.

■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNIT		
Off Characteristics									
Collector-Emitter Breakdown Voltage	BV _{CES}			650			V		
Collector Cut-Off Current	I _{CES}	V _{CE} =650V, V _{GE} =0V				5	μΑ		
G-E Leakage Current	I_{GES}	V _{CE} =0V, V _{GE} =±20V				±100	nA		
On Characteristics									
Gate to Emitter Threshold Voltage	$V_{GE(TH)}$	I _C =250μA, V _{CE} =V _{GE}				6.5	V		
Collector to Emitter Saturation Voltage	\/	I _C =7.0A, V _{GE} =15V	T _C =25°C		1.6	2.1	V		
Collector to Efflitter Saturation Voltage	$V_{CE(SAT)}$		T _C =125°C		2.0		V		
Dynamic Characteristics									
Input Capacitance	C _{IES}	V _{CE} =25V, V _{GE} =0V, f=1MHz			401		pF		
Output Capacitance	Coes				18.7		pF		
Reverse Transfer Capacitance	Cres				7.1		pF		
Switching Characteristics									
Total Gate Charge	\mathbf{Q}_{G}	V _{CE} =520V, I _C =7.0A, V _{GE} =15V			39		nC		
Gate-Emitter Charge	Q_GE				12		nC		
Gate-Collector Charge	Q_{GC}				14		nC		
Turn-On Delay Time	t _{DON)}				2.7		ns		
Rise Time	t _R	V_{CC} =400V, I_{C} =7.0A, R_{G} =5 Ω ,			12		ns		
Turn-Off Delay Time	t _{DOFF)}				16		ns		
Fall Time	t _F	V _{GE} =0~15V, L=500μH			209		ns		
Turn-On Switching Loss	Eon				0.18		mJ		
Turn-Off Switching Loss	Eoff				0.21		mJ		

^{2.} Pulse width limited by maximum junction temperature.

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